

Notic of R ferences Cited	Application/Control N 10/013,088	Applicant(s)/Patent Under Reexamination WU, XIAOJU	
	Examiner Anh D. Mai	Art Unit 2814	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	K	US-			
	L	US-			
	M	US-			

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.